

General Description

The WSD40190DN56G advanced SGT technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

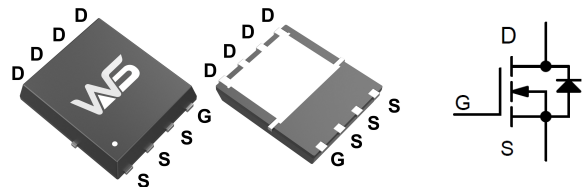
Product Summary

BVDSS	RDS(ON)	ID
40V	1.25mΩ	190A

Applications

- Battery protection
- Load switch
- Uninterruptible power supply

DFN5X6-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	190	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	130	A
I _{DM}	Pulsed Drain Current ²	400	A
EAS	Single Pulse Avalanche Energy ³	259	mJ
I _{AS}	Avalanche Current	72	A
P _D @T _C =25°C	Total Power Dissipation ⁴	96	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	55	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	1.3	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

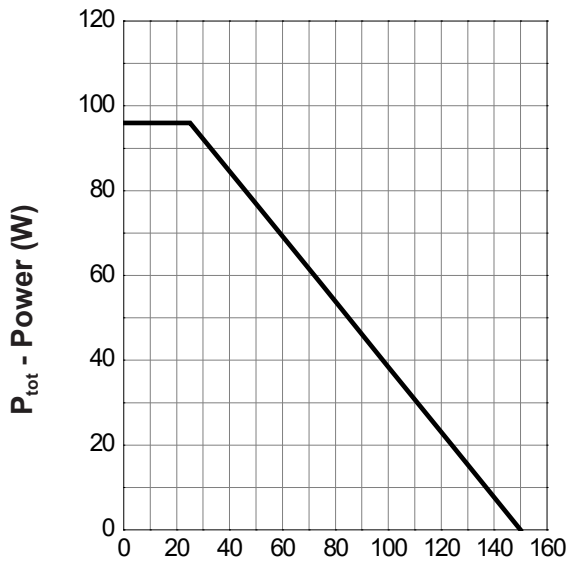
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	40	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.043	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	---	1.25	1.6	mΩ
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =15A	---	1.8	2.7	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	---	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-6.94	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =32V, V _{GS} =0V, T _J =25°C	---	---	2	uA
		V _{DS} =32V, V _{GS} =0V, T _J =55°C	---	---	10	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =15A	---	70	---	S
Q _g	Total Gate Charge	V _{DS} =20V, V _{GS} =10V, I _D =20A	---	78	---	nC
Q _g	Total Gate Charge	V _{DS} =20V, V _{GS} =4.5V, I _D =20A	---	35	---	nC
Q _{gs}	Gate-Source Charge		---	15	---	
Q _{gd}	Gate-Drain Charge		---	9	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =20V, V _{GEN} =10V, R _G =16Ω, I _D =1A, RL=20Ω.	---	22	---	ns
T _r	Rise Time		---	12	---	
T _{d(off)}	Turn-Off Delay Time		---	86	---	
T _f	Fall Time		---	84	---	
C _{iss}	Input Capacitance	V _{DS} =20V, V _{GS} =0V, f=1MHz	---	5400	---	pF
C _{oss}	Output Capacitance		---	1200	---	
C _{rss}	Reverse Transfer Capacitance		---	180	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	87	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =20A, T _J =25°C	---	---	1.3	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≦ 300us, duty cycle ≦ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=20V, V_{GS}=10V, L=0.1mH, I_{AS}=72A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

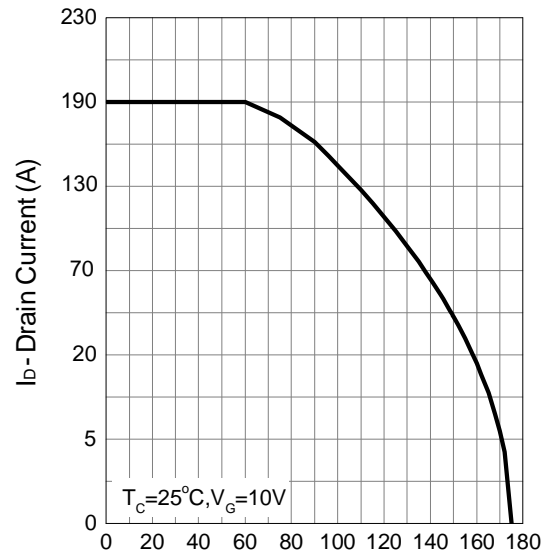
Typical Characteristics

Power Dissipation



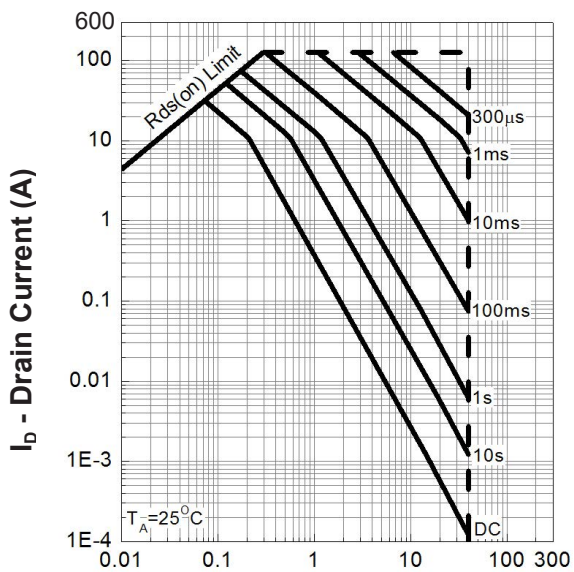
T_c - Case Temperature (°C)

Drain Current



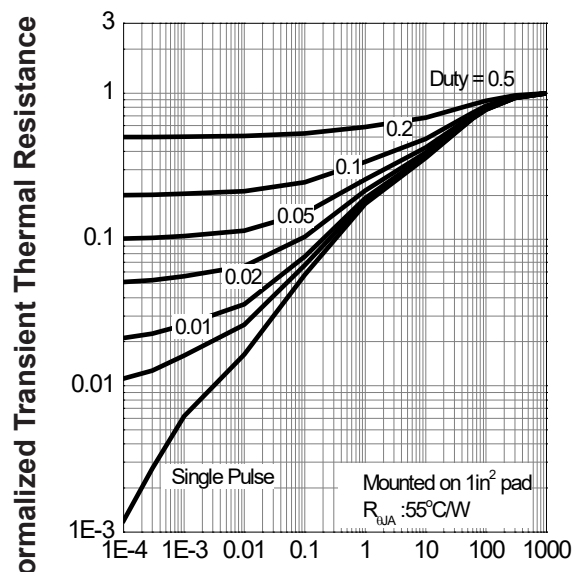
T_j - Junction Temperature (°C)

Safe Operation Area



V_{DS} - Drain - Source Voltage (V)

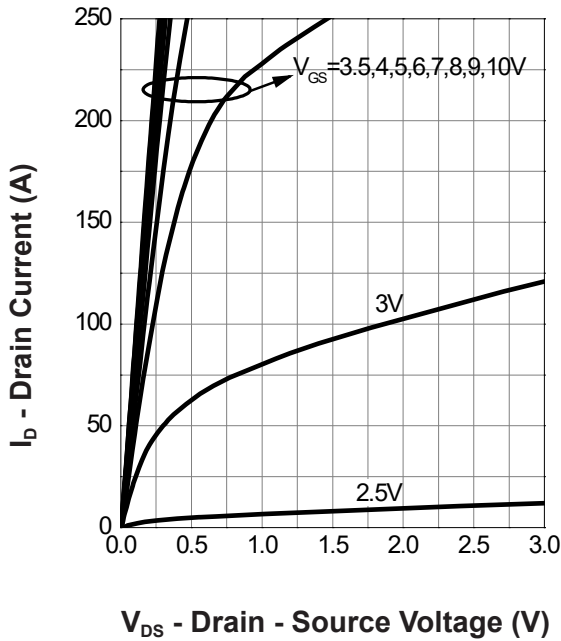
Thermal Transient Impedance



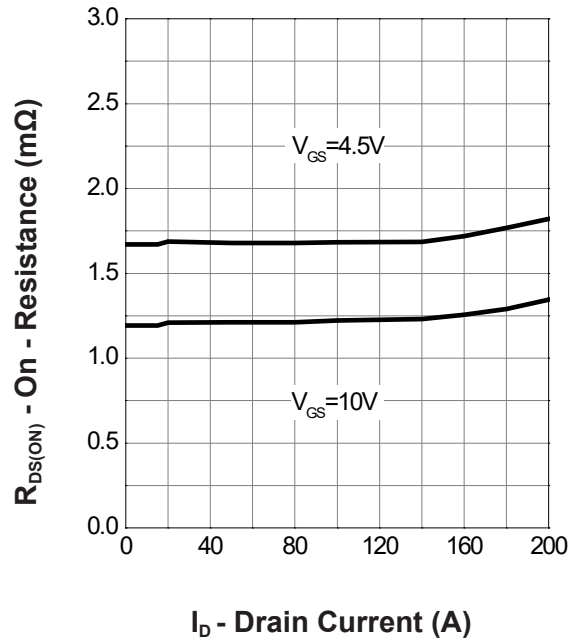
Square Wave Pulse Duration (sec)

Typical Characteristics

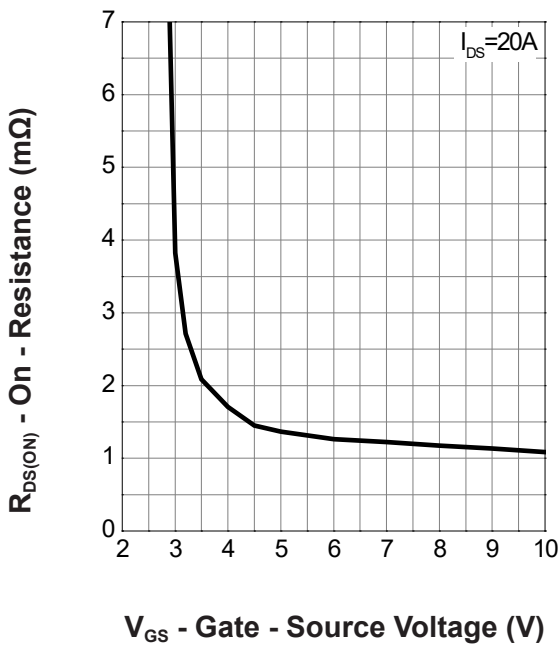
Output Characteristics



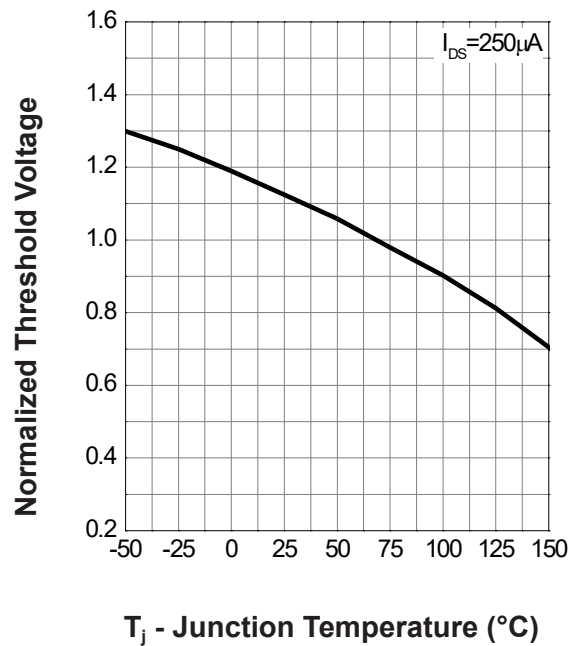
Drain-Source On Resistance



Gate-Source On Resistance

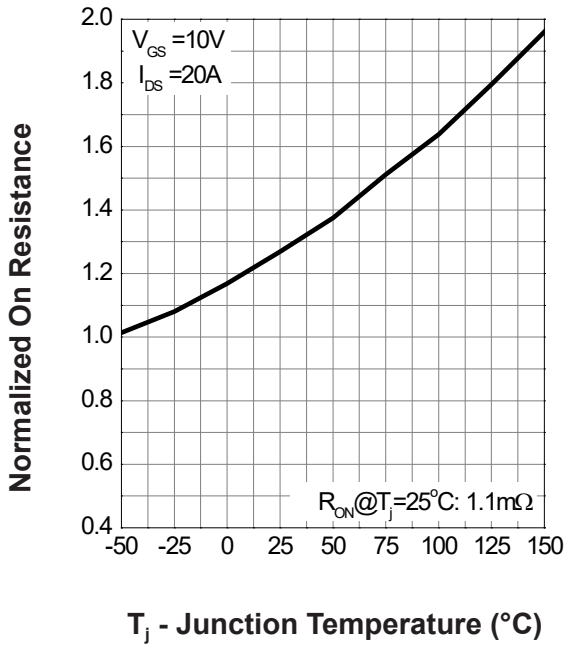


Gate Threshold Voltage

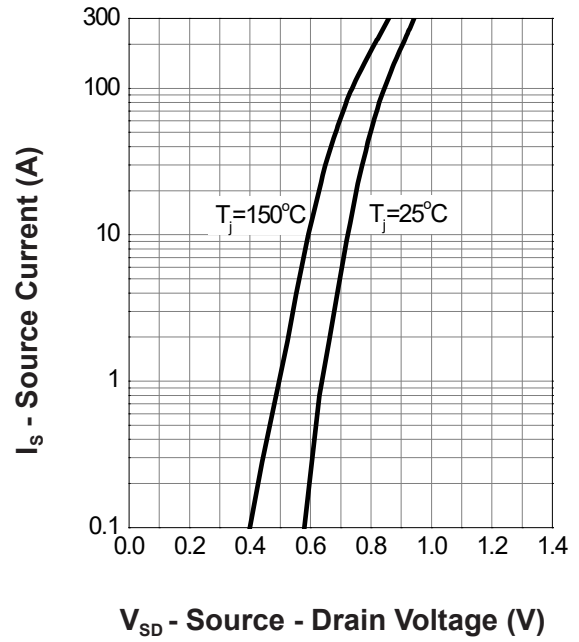


Typical Characteristics

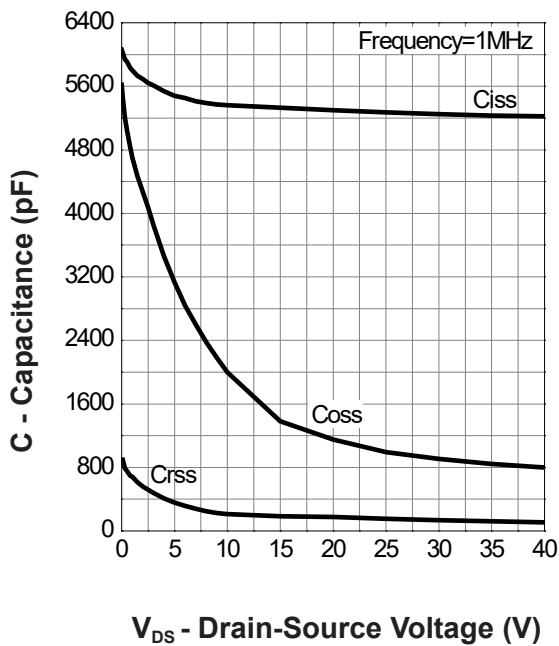
Drain-Source On Resistance



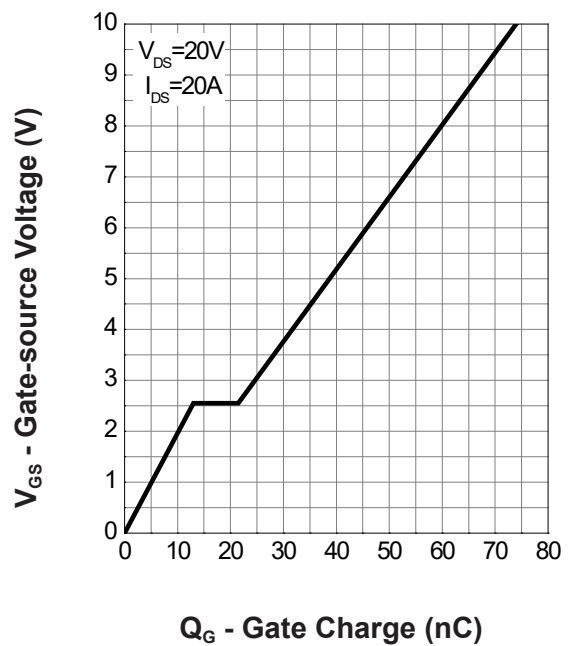
Source-Drain Diode Forward



Capacitance



Gate Charge





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